



*The SST12LP14 is a high-performance power amplifier IC based on the highly-reliable InGaP/GaAs HBT technology. Easily configured for high-power, high-efficiency applications with superb power-added efficiency, it typically provides 30 dB gain with 22% power added efficiency. The SST12LP14 has excellent linearity while meeting 802.11g spectrum mask at 23 dBm. It is ideal for the final stage power amplification in battery-powered 802.11g/b WLAN transmitter applications, and is offered in 16-contact VQFN package.*

## Features

- **High Gain:**
  - Typically 30 dB gain across 2.4~2.5 GHz over temperature 0°C to +80°C
- **High linear output power:**
  - >26.5 dBm P1dB
  - Meets 802.11g OFDM ACPR requirement up to 23 dBm
  - Added EVM ~4% up to 20 dBm for 54 Mbps 802.11g signal
  - Meets 802.11b ACPR requirement up to 24 dBm
- **High power-added efficiency/Low operating current for both 802.11g/b applications**
  - ~22% @  $P_{OUT} = 22$  dBm for 802.11g
  - ~26% @  $P_{OUT} = 23.5$  dBm for 802.11b
- **Built-in Ultra-low  $I_{REF}$  power-up/down control**
  - $I_{REF} < 4$  mA
- **Low idle current**
  - ~60 mA  $I_{CQ}$
- **High-speed power-up/down**
  - Turn on/off time (10%~90%) <100 ns
  - Typical power-up/down delay with driver delay included <200 ns
- **High temperature stability**
  - ~1 dB gain/power variation between 0°C to +80°C
  - ~1 dB detector variation over 0°C to +80°C
- **Low shut-down current (< 0.1  $\mu$ A)**
- **On-chip power detection**
- **25 dB dynamic range on-chip power detection**
- **Simple input/output matching**
- **Packages available**
  - 16-contact VQFN (3mm x 3mm)
  - Non-Pb (lead-free) packages available

## Applications

- **WLAN (IEEE 802.11g/b)**
- **Home RF**
- **Cordless phones**
- **2.4 GHz ISM wireless equipment**



## Product Description

The SST12LP14 is a high-performance power amplifier IC based on the highly-reliable InGaP/GaAs HBT technology.

The SST12LP14 can be easily configured for high-power, high-efficiency applications with superb power-added efficiency while operating over the 2.4~2.5 GHz frequency band. It typically provides 30 dB gain with 22% power-added efficiency @  $P_{OUT} = 22$  dBm for 802.11g and 27% power-added efficiency @  $P_{OUT} = 24$  dBm for 802.11b.

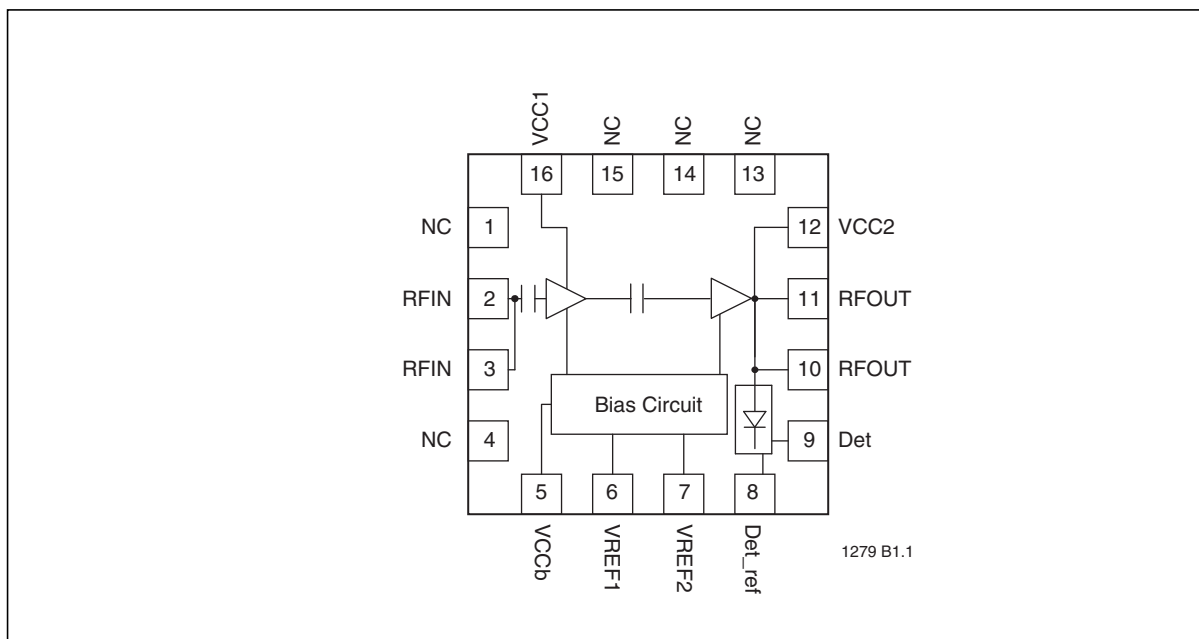
The SST12LP14 has excellent linearity, typically <4% added EVM up to 20 dBm output power which is essential for 54 Mbps 802.11g operation while meeting 802.11g spectrum mask at 23 dBm. The SST12LP14 also has wide-range (>25 dB), temperature-stable (~1 dB over 80°C), single-ended/differential power detectors which lower users' cost on power control.

The power amplifier IC also features easy board-level usage along with high-speed power-up/down control. Ultra-low reference current (total  $I_{REF} < 4$  mA) makes the SST12LP14 controllable by an on/off switching signal directly from the baseband chip. These features coupled with low operating current make the SST12LP14 ideal for the final stage power amplification in battery-powered 802.11g/b WLAN transmitter applications.

The SST12LP14 is offered in 16-contact VQFN package. See Figure 2 for pin assignments and Table 1 for pin descriptions.



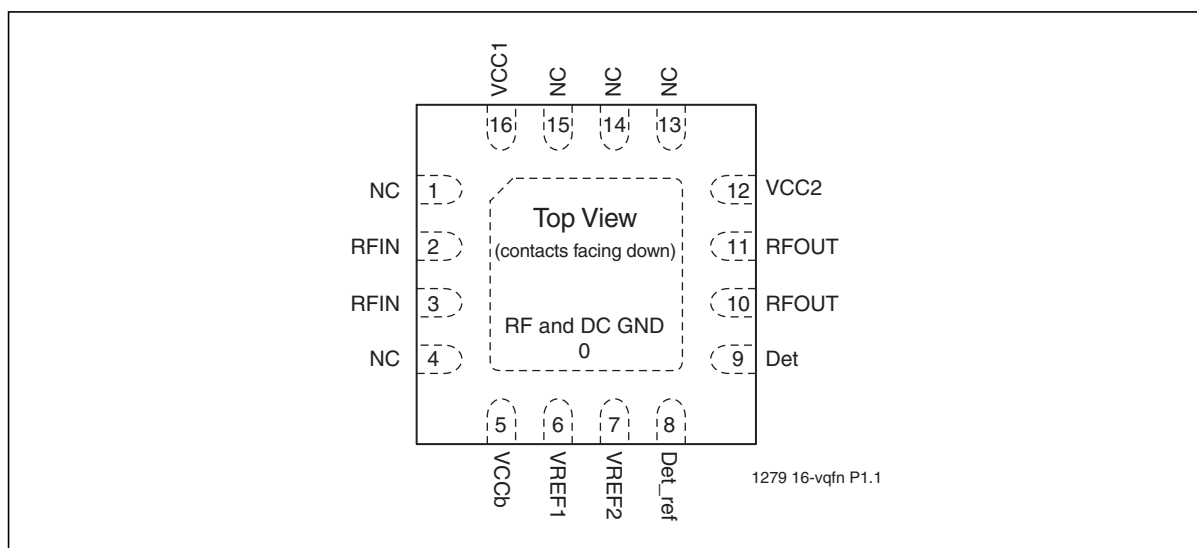
## Functional Blocks



**Figure 1:** Functional Block Diagram



## Pin Assignments



**Figure 2:** Pin Assignments for 16-contact VQFN

## Pin Descriptions

**Table 1:** Pin Description

| Symbol  | Pin No. | Pin Name      | Type <sup>1</sup> | Function                                                                                          |
|---------|---------|---------------|-------------------|---------------------------------------------------------------------------------------------------|
| GND     | 0       | Ground        |                   | The center pad should be connected to RF ground with several low inductance, low resistance vias. |
| NC      | 1       | No Connection |                   | Unconnected pins.                                                                                 |
| RFIN    | 2       |               | I                 | RF input, DC decoupled                                                                            |
| RFIN    | 3       |               | I                 | RF input, DC decoupled                                                                            |
| NC      | 4       | No Connection |                   | Unconnected pins.                                                                                 |
| VCCb    | 5       | Power Supply  | PWR               | Supply voltage for bias circuit                                                                   |
| VREF1   | 6       |               | PWR               | 1st stage idle current control                                                                    |
| VREF2   | 7       |               | PWR               | 2nd stage idle current control                                                                    |
| Det_ref | 8       |               | O                 | On-chip power detector reference                                                                  |
| Det     | 9       |               | O                 | On-chip power detector                                                                            |
| RFOUT   | 10      |               | O                 | RF output                                                                                         |
| RFOUT   | 11      |               | O                 | RF output                                                                                         |
| VCC2    | 12      | Power Supply  | PWR               | Power supply, 2nd stage                                                                           |
| NC      | 13      | No Connection |                   | Unconnected pins.                                                                                 |
| NC      | 14      | No Connection |                   | Unconnected pins.                                                                                 |
| NC      | 15      | No Connection |                   | Unconnected pins.                                                                                 |
| VCC1    | 16      | Power Supply  | PWR               | Power supply, 1st stage                                                                           |

1. I=Input, O=Output



## Electrical Specifications

The AC and DC specifications for the power amplifier interface signals. Refer to Table 3 for the DC voltage and current specifications. Refer to Figures 3 through 13 for the RF performance.

**Absolute Maximum Stress Ratings** (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

|                                                                    |                                                    |
|--------------------------------------------------------------------|----------------------------------------------------|
| Supply Voltage at pins 5, 12, and 16 ( $V_{CC}$ )                  | -0.3V to +4.6V                                     |
| Reference voltage to pin 6 ( $V_{REF1}$ ) and pin 7 ( $V_{REF2}$ ) | -0.3V to +3.6V                                     |
| DC supply current ( $I_{CC}$ )                                     | 500 mA                                             |
| Operating Temperature ( $T_A$ )                                    | -40°C to +85°C                                     |
| Storage Temperature ( $T_{STG}$ )                                  | -40°C to +120°C                                    |
| Maximum Junction Temperature ( $T_J$ )                             | +150°C                                             |
| Surface Mount Solder Reflow Temperature:                           | “with-Pb” units <sup>1</sup> : 240°C for 3 seconds |
|                                                                    | “non-Pb” units: 260°C for 3 seconds                |

1. Certain “with-Pb” package types are capable of 260°C for 3 seconds; please consult the factory for the latest information.

**Table 2: Operating Range**

| Range      | Ambient Temp   | $V_{DD}$ |
|------------|----------------|----------|
| Industrial | -40°C to +85°C | 3.3V     |

T2.1 75031

**Table 3: DC Electrical Characteristics**

| Symbol     | Parameter                                           | Min. | Typ | Max. | Unit | Test Conditions |
|------------|-----------------------------------------------------|------|-----|------|------|-----------------|
| $V_{CC}$   | Supply Voltage at pins 5, 12, 16                    | 3.0  | 3.3 | 4.2  | V    |                 |
| $I_{CC}$   | Supply Current<br>for 802.11g, 24 dBm               |      |     | 290  | mA   |                 |
|            | for 802.11g, 25 dBm                                 |      |     | 340  | mA   |                 |
| $I_{CQ}$   | Idle current for 802.11g to meet EVM @ 20.5 dBm     |      | 55  |      | mA   |                 |
| $I_{OFF}$  | Shut down current                                   |      |     | 0.1  | μA   |                 |
| $V_{REG1}$ | Reference Voltage for 1st Stage, with 120Ω resistor | 2.7  | 2.9 | 3.1  | V    |                 |
| $V_{REG2}$ | Reference Voltage for 2nd Stage, with 360Ω resistor | 2.7  | 2.9 | 3.1  | V    |                 |
| $V_{REG1}$ | Reference Voltage for 1st Stage, with 220Ω resistor | 2.9  | 3.1 | 3.3  | V    |                 |
| $V_{REG2}$ | Reference Voltage for 2nd Stage, with 590Ω resistor | 2.9  | 3.1 | 3.3  | V    |                 |

T3.0 75031



## 2.4 GHz Power Amplifier

### SST12LP14

Data Sheet

**Table 4:** AC Electrical Characteristics for Configuration

| Symbol            | Parameter                                        | Min. | Typ | Max. | Unit |
|-------------------|--------------------------------------------------|------|-----|------|------|
| F <sub>L-U</sub>  | Frequency range                                  | 2400 |     | 2485 | MHz  |
| P <sub>OUT</sub>  | Output power                                     |      |     |      |      |
|                   | @ PIN = -7 dBm 11b signals                       | 23   |     |      | dBm  |
|                   | @ PIN = -10 dBm 11g signals                      | 20   |     |      | dBm  |
| G                 | Small signal gain                                | 30   | 31  | 33   | dB   |
| G <sub>VAR1</sub> | Gain variation over band (2400~2485 MHz)         |      |     | ±0.5 | dB   |
| G <sub>VAR2</sub> | Gain ripple over channel (20 MHz)                |      | 0.2 |      | dB   |
| ACPR              | Meet 11b spectrum mask                           | 23   |     |      | dBm  |
|                   | Meet 11g OFDM 54 MBPS spectrum mask              | 22   |     |      | dBm  |
| Added EVM         | @ 20 dBm output with 11g OFDM 54 MBPS signal     |      | 3   |      | %    |
| 2f, 3f, 4f, 5f    | Harmonics at 22 dBm, without trapping capacitors |      |     | -40  | dBc  |

T4.0 75031



## Typical Performance Characteristics

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$

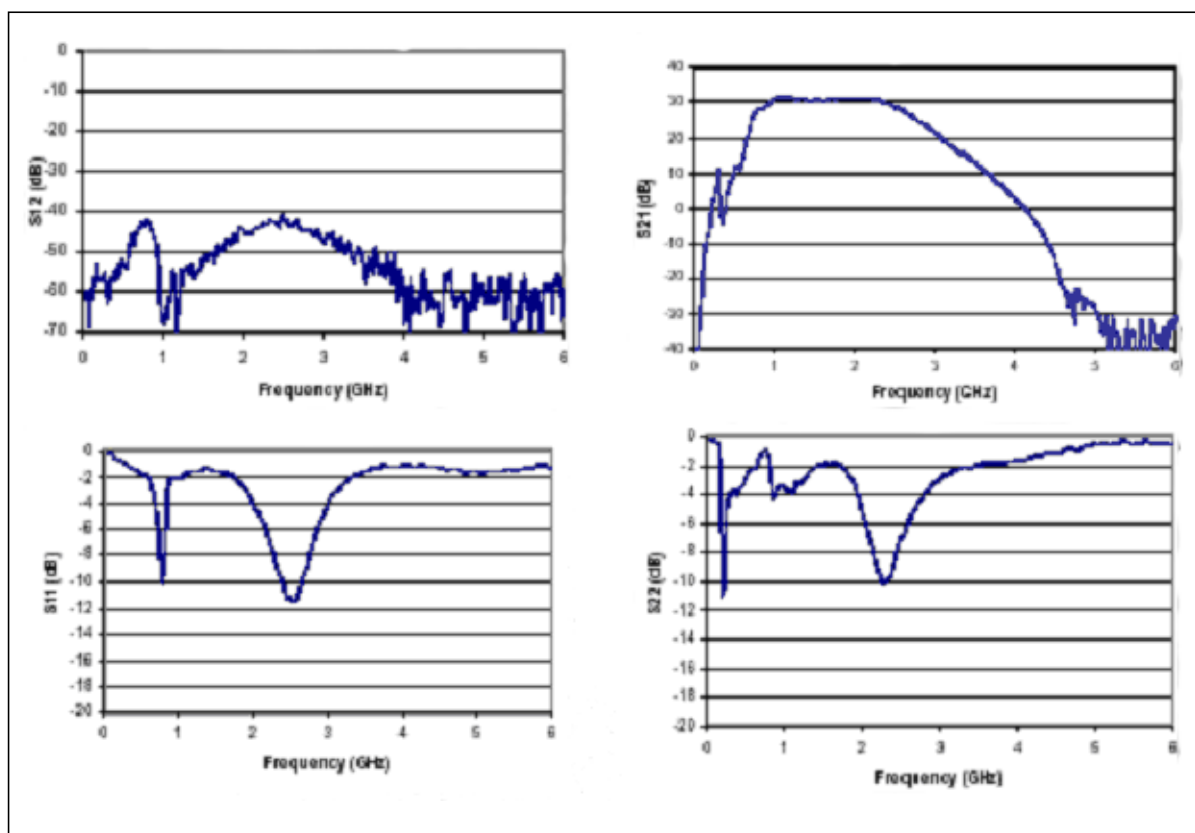


Figure 3: S-Parameters

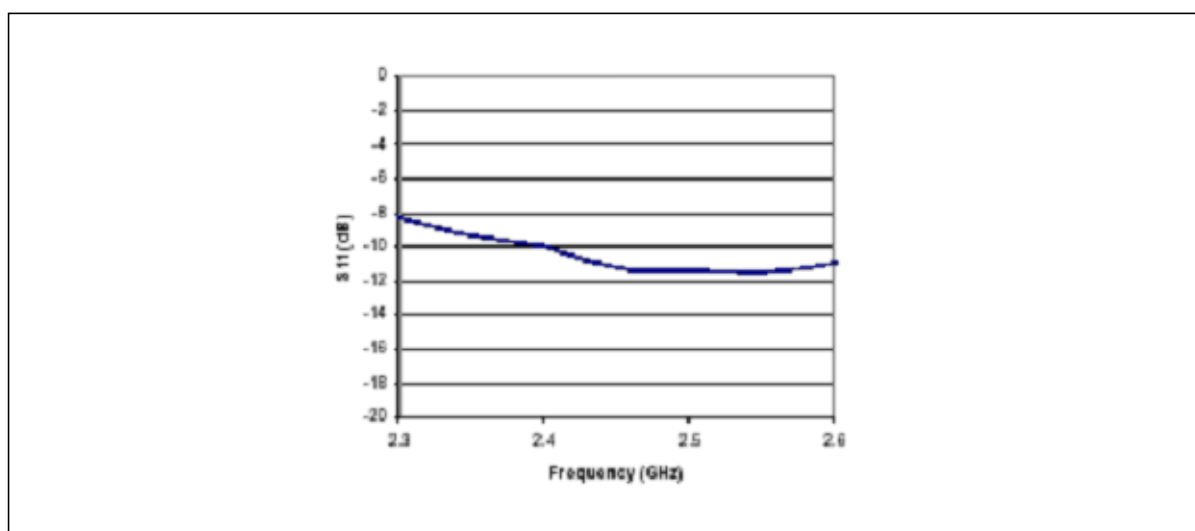
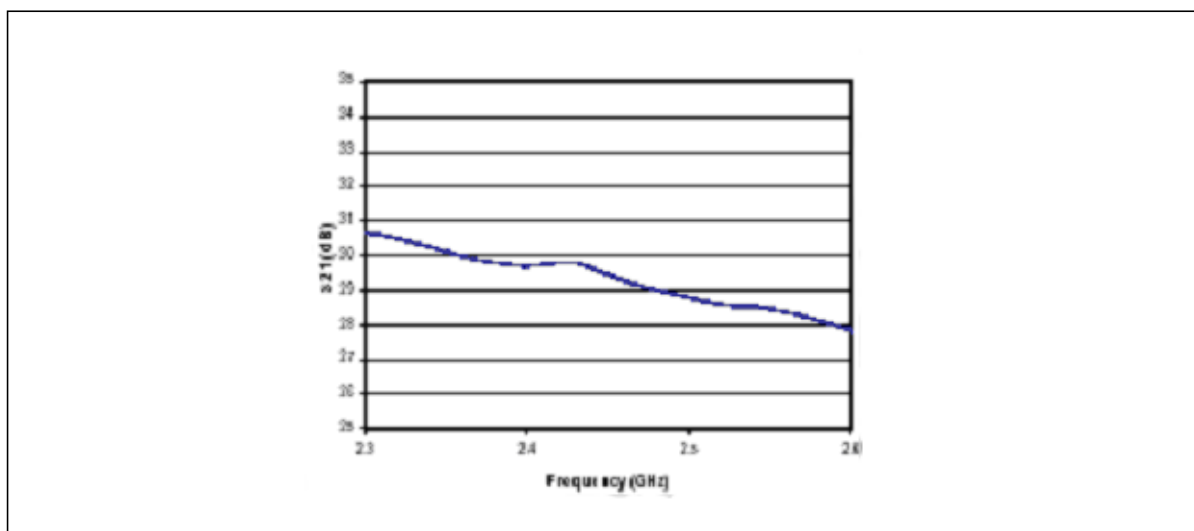


Figure 4: Input Return Loss



**Figure 5:** In-band Gain Flatness



## Typical Performance Characteristics

Test Conditions: F1 = 2.45 GHz, F2 = 2.451 GHz

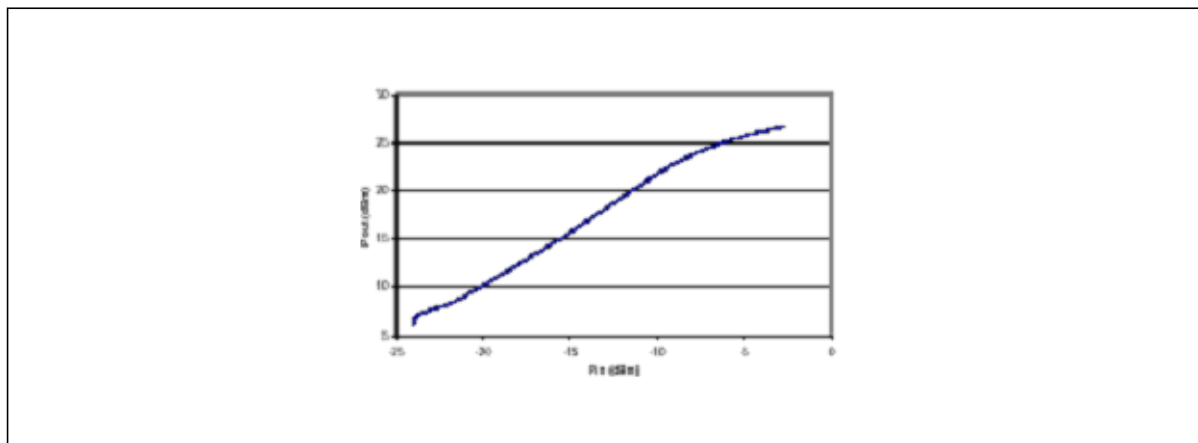


Figure 6: P<sub>OUT</sub> vs P<sub>IN</sub>

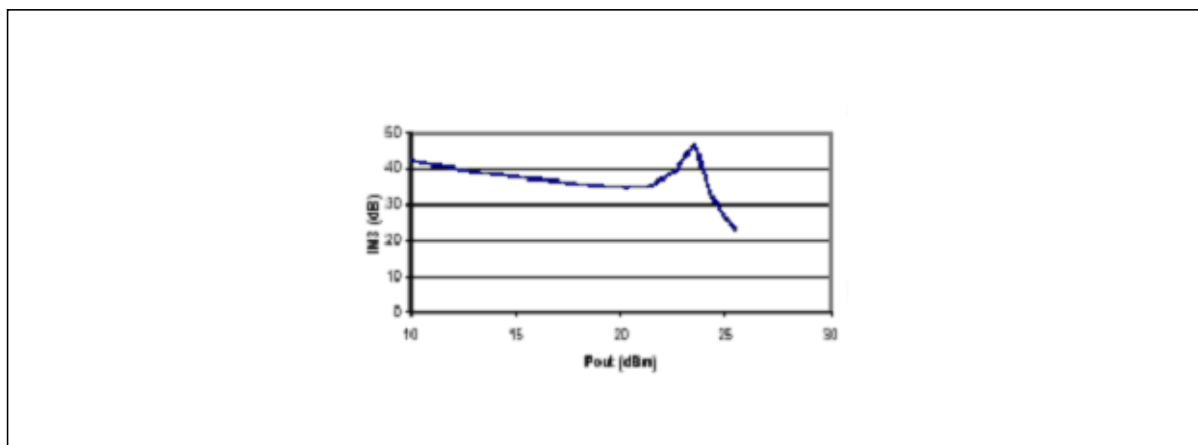
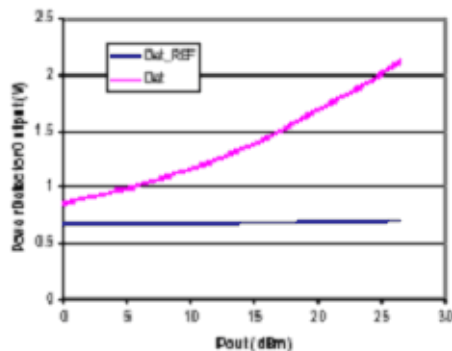
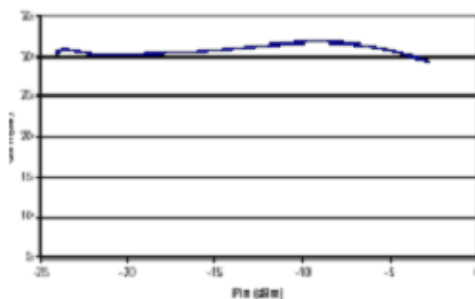


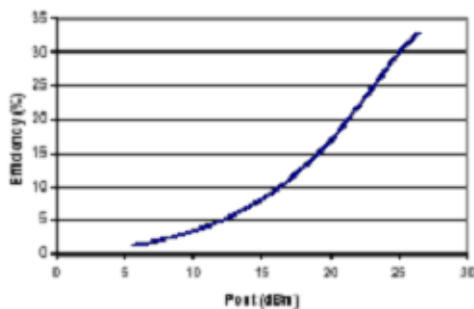
Figure 7: IM3 vs P<sub>OUT</sub>



**Figure 8:** Detectors vs P<sub>OUT</sub>



**Figure 9:** Gain vs P<sub>OUT</sub>



**Figure 10:**PAE for Two Tone



## Typical Performance Characteristics

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ ,  $F = 2.45$  GHz, 54 Mbps 802.11g OFDM signal

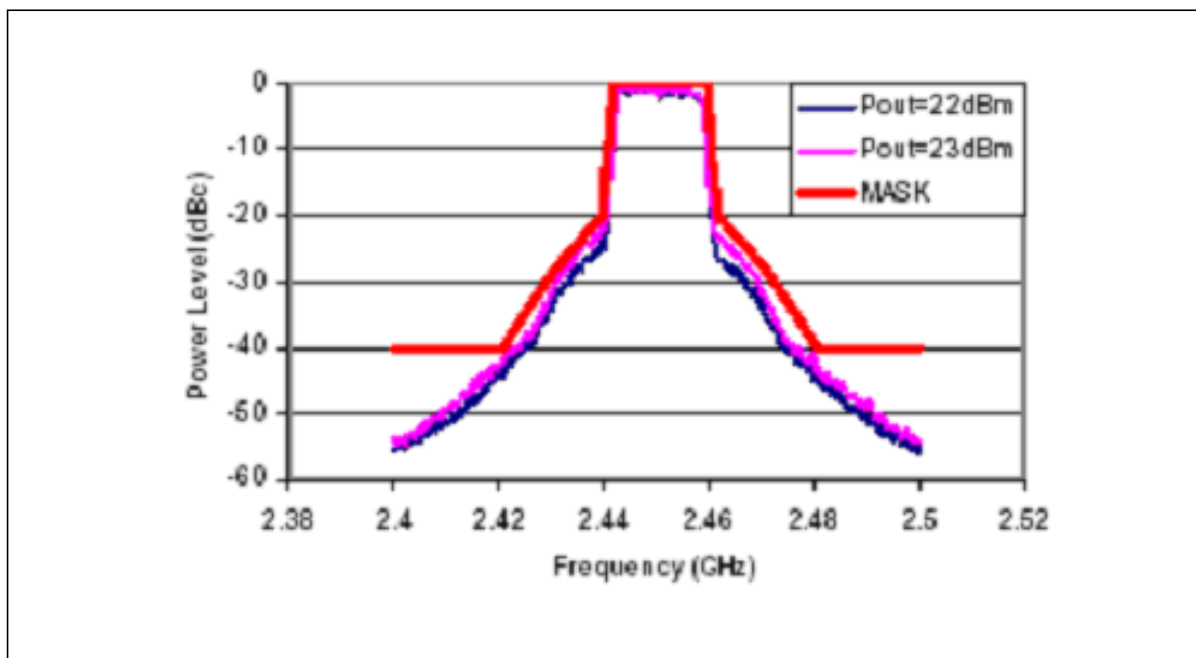


Figure 11: 802.11g Spectrum at 22/23 dBm, DC current 210/240 mA

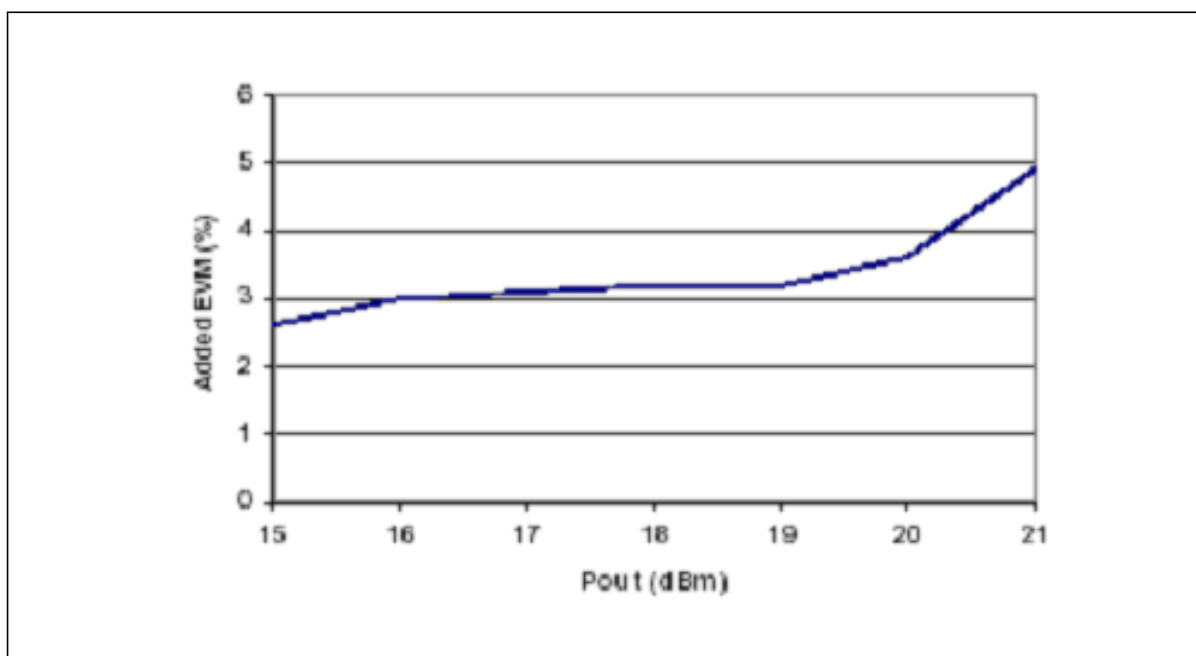
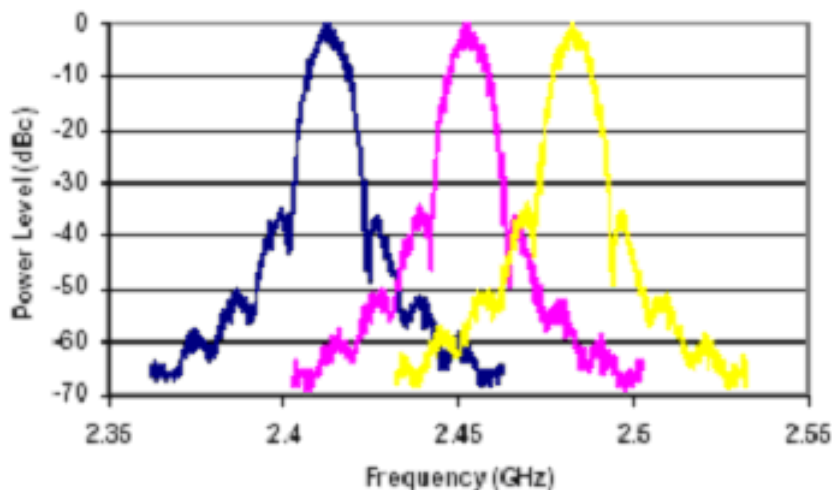


Figure 12: 802.11g Added EVM for 54 Mbps 802.11g Signal

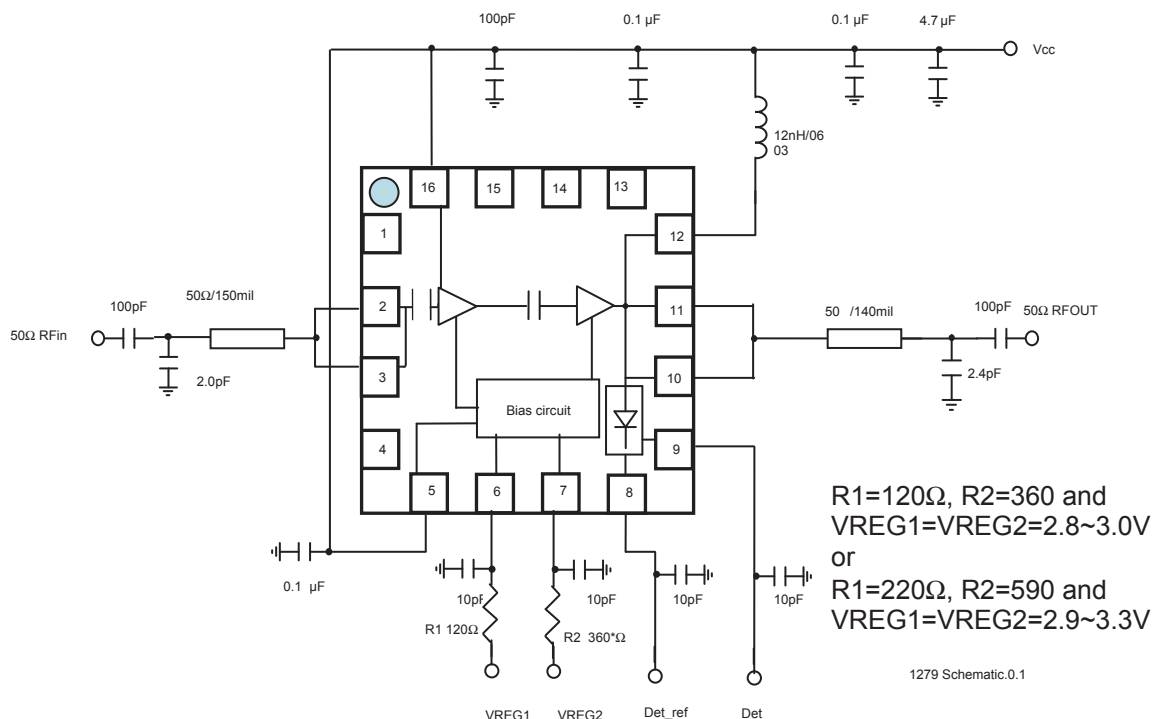


SST12LP14

## Data Sheet



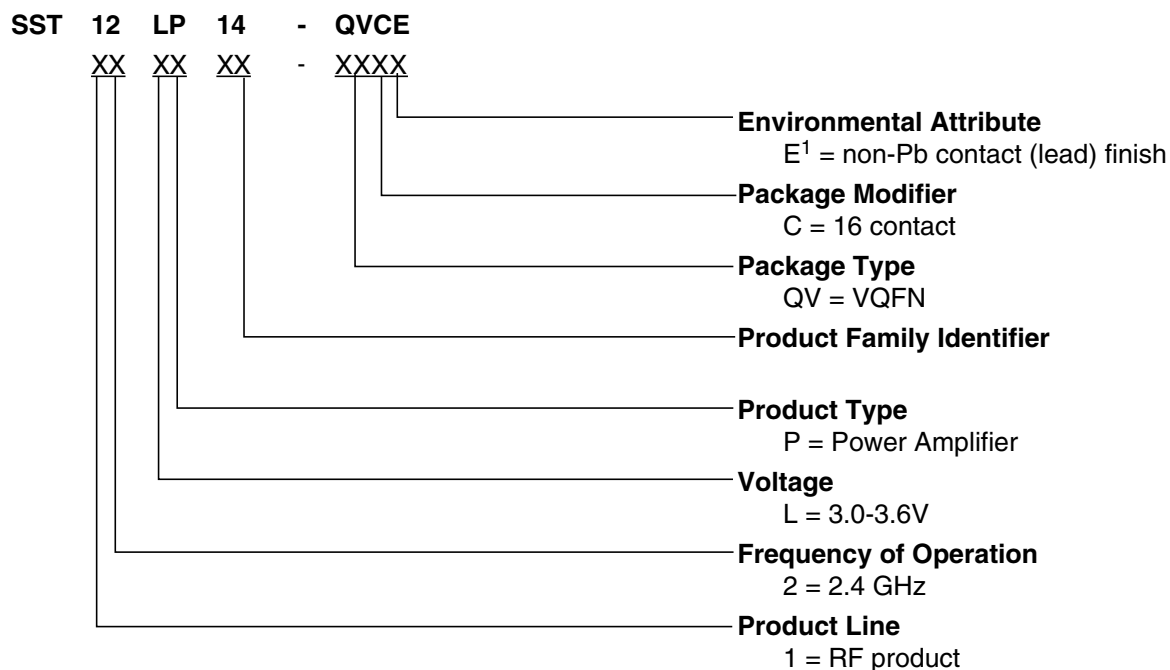
**Figure 13:802.11b Spectrum at 24 dBm, DC current consumption 280 mA**



**Figure 14:** Typical Schematic for High-Power, High-Efficiency 802.11b/g Applications



### Product Ordering Information



1. Environmental suffix "E" denotes non-Pb solder. SST non-Pb solder devices are "RoHS Compliant".

### Valid combinations for SST12LP14

SST12LP14-QVC  
SST12LP14-QVCE

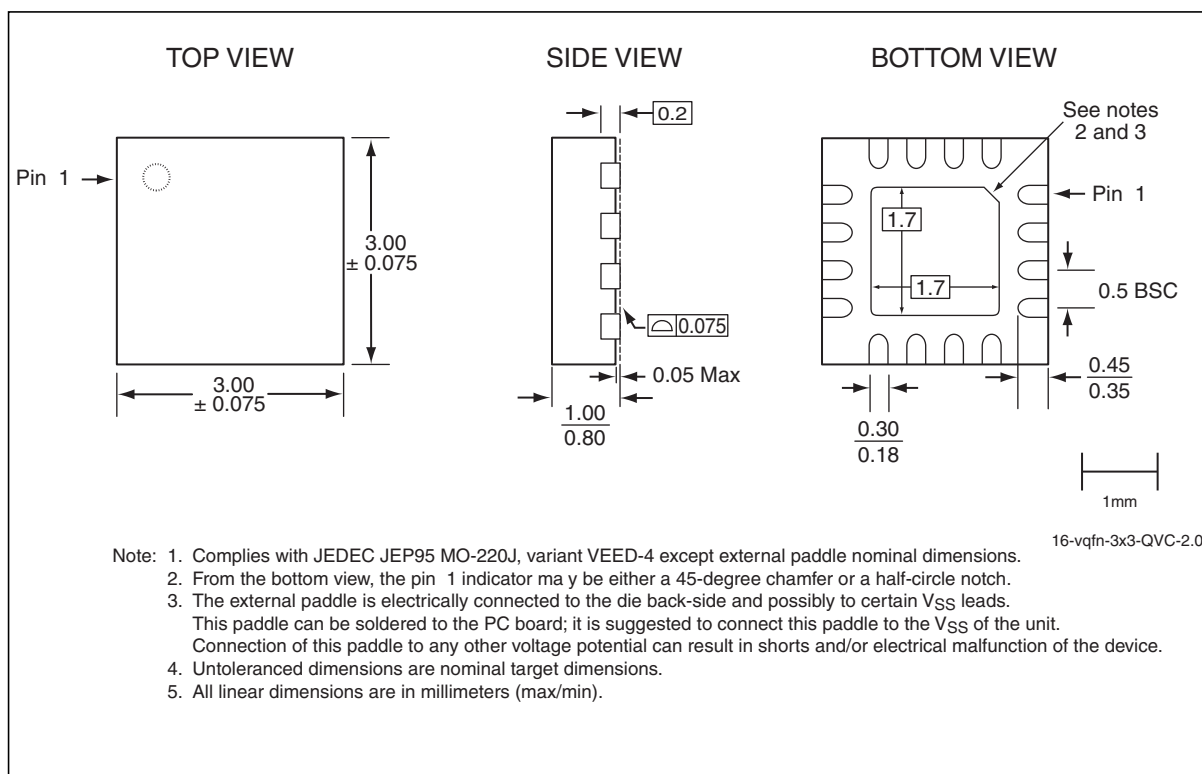
### SST12LP14 Evaluation Kits

SST12LP14-QVC-K  
SST12LP14-QVCE-K

**Note:** Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.



## Packaging Diagrams



**Figure 15:16-Contact Very-thin Quad Flat No-lead (VQFN)**  
SST Package Code: QVC



## 2.4 GHz Power Amplifier

### SST12LP14

Data Sheet

**Table 5:**Revision History

| Revision | Description                                                                                                                       | Date     |
|----------|-----------------------------------------------------------------------------------------------------------------------------------|----------|
| 00       | • DS75031: SST conversion of data sheet GP1214                                                                                    | Jan 2005 |
| 01       | • Updated document status from Preliminary Specification to Data Sheet                                                            | Apr 2008 |
| 02       | • Updated "Contact Information" on page 12.                                                                                       | Feb 2009 |
| A        | • Applied new document format<br>• Released document under letter revision system<br>• Updated Spec number from S71279 to DS75031 | Oct 2011 |

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